



## InGaAs Photodetector 10000 μm ( TO-CAN)

### Features

- Bright Surface 10000μm
- Long Wavelength Operation
- Low Dark Current
- High Responsivity
- RoHs

### Application

- For Near-infrared Sensing
- Monitoring and Meter
- Optical Instruments
- Power Monitoring

The 10000μm InGaAs Photodetector has high linearity ,high responsivity ,low return,low loss distortion.

### Absolute Maximum Ratings (Tc=25°C .unless otherwise specified)

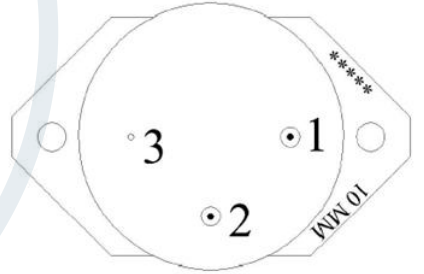
Parameter	Symbol	Min.	Max.	Unit	Test Condition
Forward Current	I <sub>FP</sub>	-	10	mA	CW
Reverse Current	I <sub>R</sub>		10	mA	CW
Operating Temperature	T <sub>OP</sub>	-20	+70	°C	-
Storage Temperature	T <sub>stg</sub>	-40	+100	°C	-
Soldering Temperature/Time	-	260/10		°C/S	-

## Specifications (electrical & optical characteristics ) T= 25°C

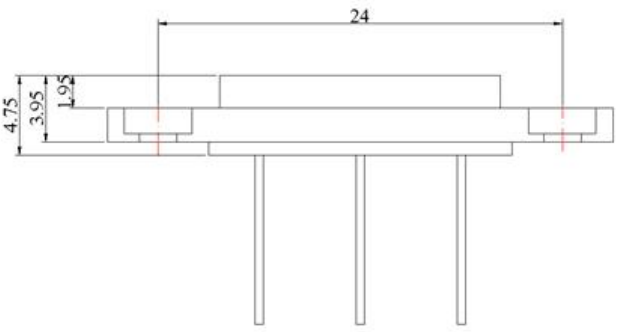
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Active Area	$\Phi$	-	10000	-	$\mu\text{m}$	-
Wavelength Range	$\lambda$	1000	-	1680	nm	-
Saturated Optical Power	$P_s$	10	-	-	dBm	$V_R=0V$
Reverse Breakdown V	$V_{BR}$	35	-	-	V	$I_D=10\mu\text{A}, \phi_e=0$
Dark Current	$I_d$	-	-	1000	nA	$V_R=5V$
Responsivity	R	0.85 @ 1310nm			A / W	$\phi_e=100\mu\text{w}, \lambda=1310\text{nm}$
		0.90 @1550nm				$\phi_e=100\mu\text{w}, \lambda=1550\text{nm}$
Capacitance	$C_t$	-	-	500	pF	$V_R=5V, f=1\text{MHz}$
Input Power Range	P	-60	-	+10	dBm	$V_R=5V$



### Pin Assignment



- 1.PD+
- 2.PD-
- 3.CASE

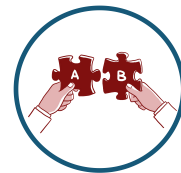


### Order Information

GTA2010R (InGaAs Pin 10000um)



Please let us know your request details before order.



Customize for you

